

AMENDMENTS

In the Claims:

Please amend claims 1-11 and add new claims 12-15 as follows:

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1. (Amended) A gallium nitride compound semiconductor light-emitting diode comprising:

- a substrate;
- an n-type electrode region comprising an n-type transmissive electrode;
- a gallium nitride compound semiconductor multilayer structure including an active layer; and
- a p-type electrode region comprising a p-type transmissive electrode, wherein the n-type transmissive electrode and p-type transmissive electrode are films so as to be substantially transparent.

2. (Amended) A gallium nitride compound light-emitting diode according to claim 1, wherein the p-type transmissive electrode and the n-type transmissive electrode transmit light which is generated in the active layer and reflected from the substrate so that the light exits the light emission device.

3. (Amended) A gallium nitride compound light-emitting diode according to claim 1, wherein the n-type transmissive electrode is located outside of the p-type transmissive electrode.

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4. (Amended) A gallium nitride compound light-emitting diode according to claim 1, wherein the n-type transmissive electrode is formed around a circumference of the p-type transmissive electrode.

5. (Amended) A gallium nitride compound light-emitting diode according to claim 1,

wherein the gallium nitride compound semiconductor multilayer structure includes a buffer layer and an n-type gallium nitride compound semiconductor layer, and

wherein the n-type transmissive electrode is formed on a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor layer in a region neighboring the buffer layer.

6. (Amended) A gallium nitride compound light-emitting diode according to claim 1,

wherein the n-type electrode region further comprises an n-type pad electrode, and wherein the p-type electrode region further comprises a p-type pad electrode.

7. (Amended) A gallium nitride compound light-emitting diode according to claim 6, wherein the n-type pad electrode and the p-type pad electrode are provided substantially along one side of a light emitting face of the gallium nitride compound semiconductor light emission device.

8. (Amended) A gallium nitride compound light-emitting diode according to claim 6, wherein the p-type pad electrode is formed in the vicinity of a center of a light emitting face of the gallium nitride compound semiconductor light emission device.

9. (Amended) A gallium nitride compound light-emitting diode according to claim 1, wherein the n-type transmissive electrode comprises a thin metal film.

10. (Amended) A gallium nitride compound light-emitting diode according to claim 6, wherein the n-type pad electrode is of a type which realizes a Schottky contact.

11. (Amended) A gallium nitride compound semiconductor light-emitting diode according to claim 6, wherein the n-type pad electrode comprises at least one material selected from the group consisting of:

Pd/Au, Ni/Au, Pt/Au, Pd/Ni/Au, Pd/Al, Ni/Al, Pt/Al, and Pd/Ni/Al

or an alloy comprising one or more material selected from the above group.

12. (New) A gallium nitride compound semiconductor light-emitting diode according to claim 1, wherein the n-type transmissive electrode and p-type transmissive electrode are of a thickness of 30 nm or less.

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13. (New) A gallium nitride compound semiconductor light-emitting diode comprising:
a substrate;
an n-type electrode region comprising an n-type transmissive electrode;
a gallium nitride compound semiconductor multilayer structure including an active layer;
and
a p-type electrode region comprising a p-type transmissive electrode, wherein
the n-type transmissive electrode is formed on a side face of the substrate, a side face of the buffer layer, and a side face of the n-type gallium nitride compound semiconductor layer in a region neighboring the buffer layer.

14. (New) A gallium nitride compound semiconductor light emitting diode according to claim 13, wherein
the n-type transmissive electrode comprises an oxide semiconductor.

15. (New) A gallium nitride compound semiconductor light-emitting diode according to claim 1, wherein the n-type transmissive electrode comprises a thick film of (ITO)